

Abstract of the Disclosure

02/318,073

A monolithically formed ferromagnetic thin-film memory is disclosed that has local shielding on at least two sides of selected magnetic storage elements. The local shielding preferably extends along the back and side surfaces of a word line and/or digital lines of a conventional magnetic memory. In this configuration, the local shielding not only may help reduce externally generated EMI, internally generated cross-talk and other unwanted fields in the magnetic bit region, but may also help enhance the desired magnetic fields in the bit region.

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By:

Jolene Alger